

BQ2946xx 用于锂离子电池的单节电池保护器

1 特性

- 用于二级保护的单节电池过压监视器
- 固定可编程延迟计时器
- 固定过压保护 (OVP) 阈值
 - 3.85V 至 4.6V 的可用范围
- 固定 OVP 延迟选项：4s 或 6.5s
- 高精度 OVP：±10mV
- 低功耗 $I_{CC} \approx 1\mu A$ ($V_{CELL(ALL)} < V_{PROTECT}$)
- 每节电池输入的泄漏电流低于 100nA
- 小封装尺寸
 - 6 引脚 SON

2 应用

- 为下列产品的锂离子电池组提供二级保护：
 - 平板电脑
 - 手写板电脑
 - 便携式设备和仪器

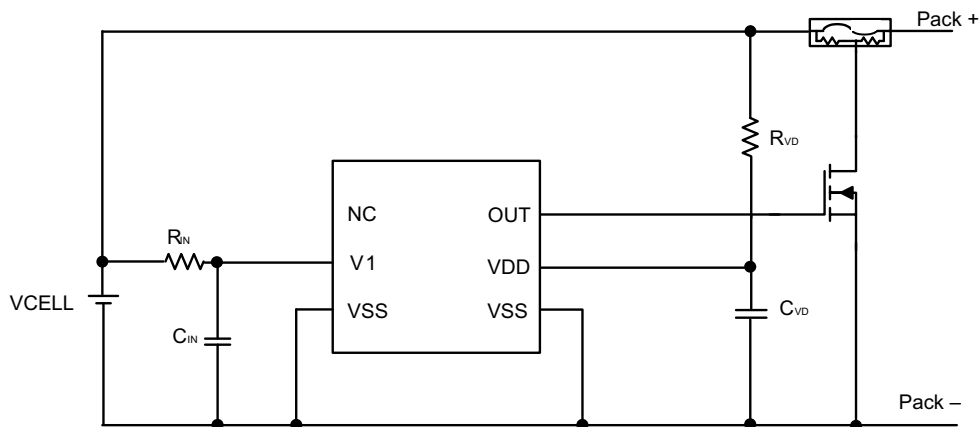
3 说明

BQ2946xx 系列产品是用于锂离子电池包系统的二级过压监控器和保护器。该系列产品监视电池的过压状况，一旦超过 OVP 阈值就触发内部计数器；在经过设置的固定延迟之后，输出转换为高电平。如果电池电压下降至低于设定阈值减去迟滞所得的值，输出将会复位（变为低电平）。

器件信息

器件型号 ⁽¹⁾	封装	封装尺寸 (标称值)
BQ294602	SON (6)	2.00mm × 2.00mm
BQ294604		
BQ294624		
BQ294682		

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



简化原理图

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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision D (April 2017) to Revision E (April 2021)	Page
• Removed PRODUCT PREVIEW devices	3

Changes from Revision C (July 2015) to Revision D (April 2017)	Page
• 在 <i>器件信息</i> 中添加了 BQ294624.....	1
• Added <i>Receiving Notification of Documentation Updates</i> section.....	13

5 Device Options

T _A	PART NUMBER	OVP (V)	DELAY TIME (s)
- 40°C to +110°C	BQ294602	4.35	4
	BQ294604	4.35	6.5
	BQ294624	4.45	6.5
	BQ294682	4.225	4

6 Pin Configuration and Functions

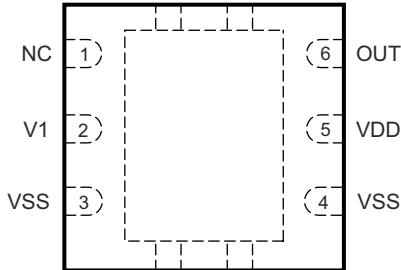


图 6-1. DRV Package 6-Pin SON Top View

表 6-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
NC	1	—	No connection
OUT	6	OA	Output drive for external N-channel FET.
PWRPAD	Thermal Pad	—	VSS pin to be connected to the PWRPAD on the printed-circuit-board (PCB) for proper operation.
V1	2	IA	Sense input for positive voltage of the cell.
VSS	3	P	Electrically connected to IC ground and negative terminal of the cell.
VSS	4	P	Electrically connected to IC ground and negative terminal of the cell.
VDD	5	P	Power supply

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Supply voltage	VDD - VSS	- 0.3	30	V
Input voltage	V1 - VSS	- 0.3	8	V
Output voltage	OUT - VSS	- 0.3	30	V
Continuous total power dissipation, P _{TOT}		See # 7.4		
Functional temperature		- 65	110	°C
Lead temperature (soldering, 10 s), T _{SOLDER}			300	°C
Storage temperature, T _{stg}		- 65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

		VALUE	UNIT
V _(ESD) Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
	Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Supply voltage, V _{DD} ⁽¹⁾	3	8	V
Input voltage V1 - VSS	0	5	V
Operating ambient temperature, T _A	- 40	110	°C

- (1) See [# 9.2](#).

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		BQ2946xx	UNIT
		DRV (SON)	
		6 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	186.4	°C/W
R _{θJC(top)}	Junction-to-case(top) thermal resistance	90.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	110.7	°C/W
ψ _{JT}	Junction-to-top characterization parameter	96.7	°C/W
ψ _{JB}	Junction-to-board characterization parameter	90	°C/W
R _{θJC(bot)}	Junction-to-case(bottom) thermal resistance	n/a	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

7.5 Electrical Characteristics

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{DD} = 4\text{ V}$, MIN/MAX values stated where $T_A = -40^\circ\text{C}$ to $+110^\circ\text{C}$ and $V_{DD} = 4\text{ V}$ (unless otherwise noted)

TEST NO.	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
VOLTAGE PROTECTION THRESHOLD VCx								
1.0	V_{OV}	$V_{(\text{PROTECT})} - \text{Oversvoltage Detection}$	BQ294602, fixed delay 4 s, $V1 > V_{OV}$		4.35	V		
1.1			BQ294604, fixed delay 6.5 s, $V1 > V_{OV}$		4.35			
1.2			BQ294622, fixed delay 4 s, $V1 > V_{OV}^{(2)}$		4.45			
1.3			BQ294624, fixed delay 6.5 s, $V1 > V_{OV}$		4.45			
1.4			BQ294682, fixed delay 4 s, $V1 > V_{OV}$		4.225			
1.5			BQ294684, fixed delay 6.5 s, $V1 > V_{OV}^{(2)}$		4.225			
1.6	V_{HYS}	Oversvoltage Detection Hysteresis	250	300	400	V		
1.7	V_{OA}	OV Detection Accuracy	$T_A = 25^\circ\text{C}$		-10	10	mV	
1.8	$V_{OA} - \text{DRIFT}$	OV Detection Accuracy due to Temperature	$T_A = -40^\circ\text{C}$ $T_A = 0^\circ\text{C}$ $T_A = 60^\circ\text{C}$ $T_A = 110^\circ\text{C}$		-40 -20 -24 -54	44 20 24 54	mV	
SUPPLY AND LEAKAGE CURRENT								
1.9	I_{CC}	Supply Current	$(V1 - VSS) = 4.0\text{ V}$ (see 图 8-3 for reference)		1	2	μA	
			$(V1 - VSS) = 2.8\text{ V}$ with $T_A = -40^\circ\text{C}$ to $+60^\circ\text{C}$			1.25		
1.10	I_{IN}	Input Current at V1 Pins	Measured at $V1 = 4.0\text{ V}$ $(V1 - VSS) = 4.0\text{ V}$ $T_A = 0^\circ\text{C}$ to 60°C (see 图 8-3 for reference)		-0.1	0.1	μA	
OUTPUT DRIVE OUT								
1.11	V_{OUT}	Output Drive Voltage	$(V1 - VSS) > V_{OV}$ $V_{DD} = V1$, $I_{OH} = 100\ \mu\text{A}$, $T_A = -40^\circ\text{C}$ to $+110^\circ\text{C}$		$3 V_{DD} - 0.3$		V	
1.12			$(V1 - VSS) < V_{OV}$, $I_{OL} = 100\ \mu\text{A}$, $T_A = 25^\circ\text{C}$ $T_A = -40^\circ\text{C}$ to $+110^\circ\text{C}$		250	400	mV	
1.13			OUT Short Circuit Current		$OUT = 0\text{ V}$, $(V1 - VSS) > V_{OV}$		1.5	3
1.14	$I_{OUT(\text{Short})}$	OUT Short Circuit Current	$OUT = 0\text{ V}$, $(V1 - VSS) > V_{OV}$		1.5	3	mA	
1.15	t_R	Output Rise Time	$CL = 1\text{ nF}$, $V_{OH(\text{OUT})} = 0\text{ V}$ to $5\text{ V}^{(1)}$		5		μs	
1.16	Z_O	Output Impedance			2	5	$\text{k}\Omega$	
FIXED DELAY TIMER								
1.17	t_{DELAY}	Fault Detection Delay Time	Fixed Delay, BQ2946x2		3.2	4	4.8	s
			Fixed Delay, BQ2946x4		5.2	6.5	7.8	
1.18	$t_{\text{DELAY_CTM}}$	Fault Detection Delay Time in Test Mode	Fixed Delay (Internal settings)		15		ms	

- (1) Specified by design. Not 100% tested in production.
(2) Product Preview only.

7.6 Typical Characteristics

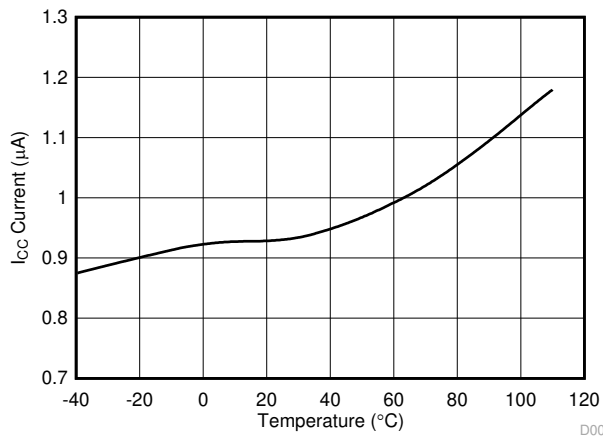


图 7-1. I_{CC} Current Consumption vs Temperature

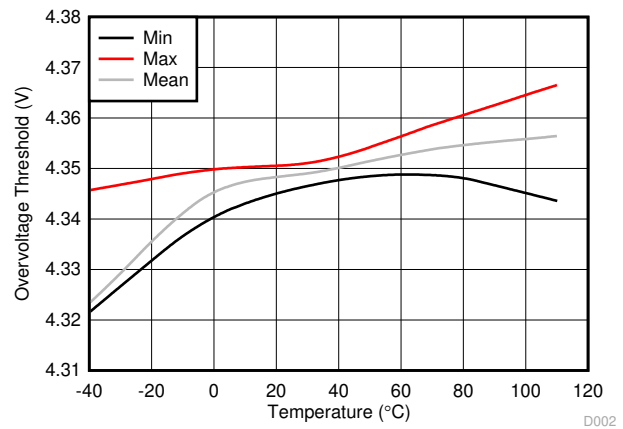


图 7-2. BQ294602 Overvoltage Threshold (OVT) vs Temperature

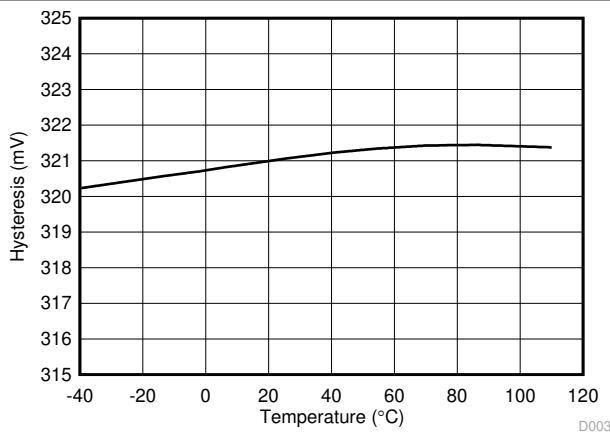


图 7-3. Hysteresis V_{HYS} vs Temperature

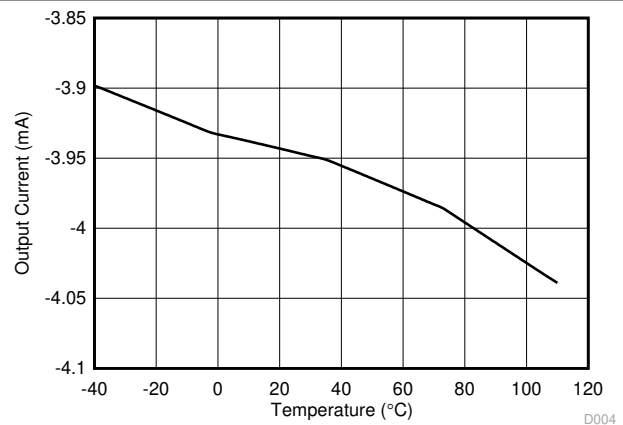


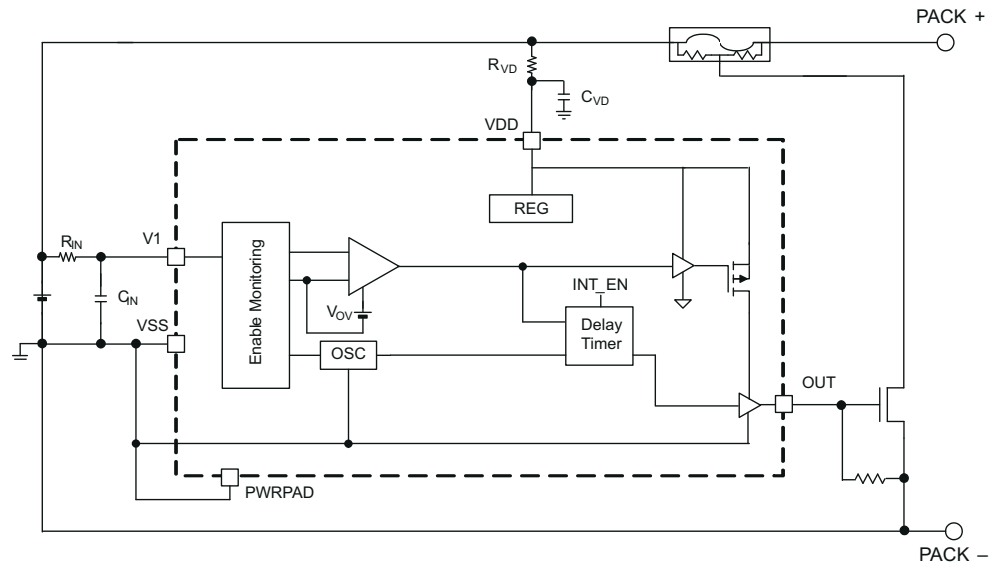
图 7-4. Output Current I_{OUT} vs Temperature

8 Detailed Description

8.1 Overview

The BQ2946xx is a second-level overvoltage (OV) protector for a single cell. The cell voltage is compared to a protection voltage threshold, V_{OV} . The protection threshold is preprogrammed at the factory with a range from 3.85 V to 4.65 V. When the OVP is triggered, the OUT pin goes high to activate an external N-channel FET, which conducts a low-impedance path to blow a fuse.

8.2 Functional Block Diagram



8.3 Feature Description

The method of overvoltage detection is comparing the cell voltage to an OVP threshold voltage V_{OV} . Once the cell voltage exceeds the programmed fixed value V_{OV} , the delay timer circuit is activated. This delay (t_{DELAY}) is fixed for 4 seconds for the BQ294602 device. When these conditions are satisfied, the OUT terminal is transitioned to a high level. This output (OUT) is released to a low condition if the cell input (V1) is below the OVP threshold minus the V_{HYS} .

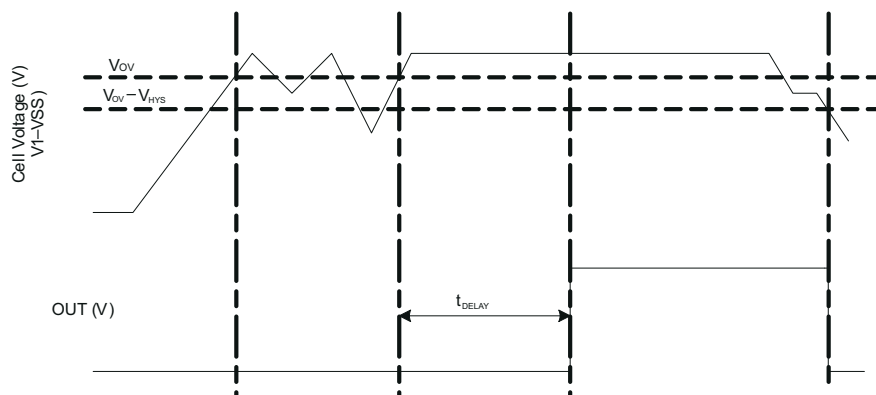


图 8-1. Timing for Overvoltage Sensing

8.3.1 Sense Positive Input for V1

This is an input to sense single battery cell voltage. A series resistor and a capacitor across the cell is required for noise filtering and stable voltage monitoring.

8.3.2 Output Drive, OUT

The gate of an external N-channel MOSFET is connected to this terminal. This output transitions to a high level when an overvoltage condition is detected and after the programmed delay timer. The OUT will reset to a low level if the cell voltage falls below the V_{OV} threshold before the fixed delay timer expires.

8.3.3 Supply Input, VDD

This terminal is the unregulated input power source for the IC. A series resistor is connected to limit the current, and a capacitor is connected to ground for noise filtering.

8.3.4 Thermal Pad, PWRPAD

For correct operation, the power pad (PWRPAD) is connected to the V_{SS} terminal on the PCB.

8.4 Device Functional Modes

8.4.1 NORMAL Mode

When the cell voltage is below the overvoltage threshold, V_{OV} , the device operates in NORMAL mode. The OUT pin is inactive and is low.

8.4.2 OVERVOLTAGE Mode

OVERVOLTAGE mode is detected if the cell voltage exceeds the overvoltage threshold, V_{OV} , for configured OV delay time. The OUT pin is activated, internally pulled high, after a delay time, t_{DELAY} . An external FET then turns on, shorting the fuse to ground, which allows the battery and/or charger power to blow the fuse. When the cell voltages fall below $(V_{OV} - V_{HYS})$, the device returns to NORMAL mode.

8.4.3 Customer Test Mode

Customer Test Mode (CTM) helps reduce test time for checking the overvoltage delay timer parameter once the circuit is implemented in the battery pack. To enter CTM, VDD should be set to at least 10 V higher than V1 (see [图 8-2](#)). The delay timer is greater than 10 ms, but considerably shorter than the timer delay in normal operation. To exit CTM, remove the VDD to V1 voltage differential of 10 V so that the decrease in this value automatically causes an exit.

CAUTION

Avoid exceeding any Absolute Maximum Voltages on any pins when placing the part into CTM. Also avoid exceeding Absolute Maximum Voltage for the cell voltage ($V1 - V_{SS}$). Stressing the pins beyond the rated limits may cause permanent damage to the device.

[图 8-2](#) shows the timing for the CTM.

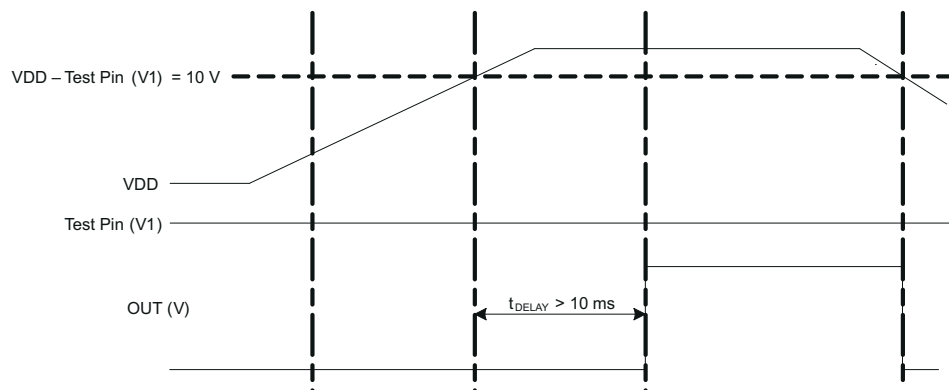


图 8-2. Timing for Customer Test Mode

[图 8-3](#) shows the measurement for current consumption for the product for both VDD and V_x .

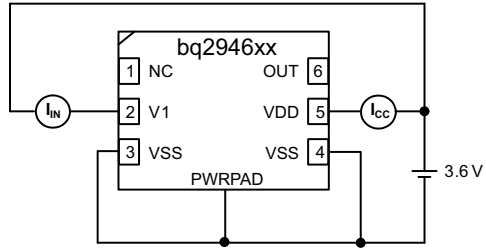


图 8-3. Configuration for IC Current Consumption Test

Application and Implementation

备注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The BQ2946xx devices are a family of second-level protectors used for overvoltage protection of the single-cell battery pack in the application. The OUT pin drives a NMOS FET that connects the fuse to ground in the event of a fault condition. This provides a shorted path to use the battery and/or charger power to blow the fuse and cut the power path.

9.1.1 Application Configuration

Changes to the ranges stated in 表 9-1 may impact the accuracy of the cell measurements. 图 9-1 shows each external component.

9.1.2

备注

Connect VSS (pins 3 and 4) externally to the CELL - terminal.

9.2 Typical Application

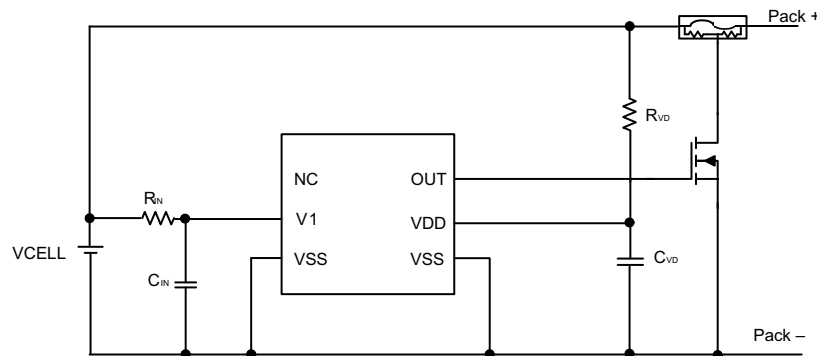


图 9-1. Application Configuration Schematic

备注

Connect VSS (pins 3 and 4) externally to the CELL - terminal.

9.2.1 Design Requirements

For this design example, use the parameters listed in 表 9-1 as the input parameters.

表 9-1. Parameters

PARAMETER	EXTERNAL COMPONENT	MIN	NOM	MAX	UNIT
Voltage monitor filter resistance	R _{IN}	900	1000	1100	Ω
Voltage monitor filter capacitance	C _{IN}	0.01	0.1		μF
Supply voltage filter resistance	R _{VD}	100		1K	Ω

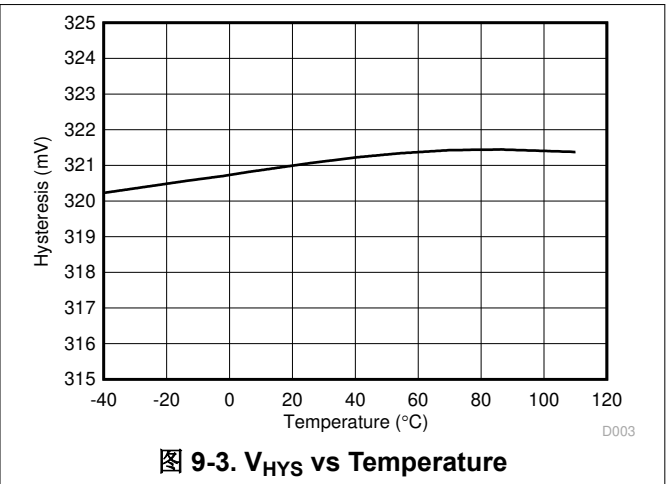
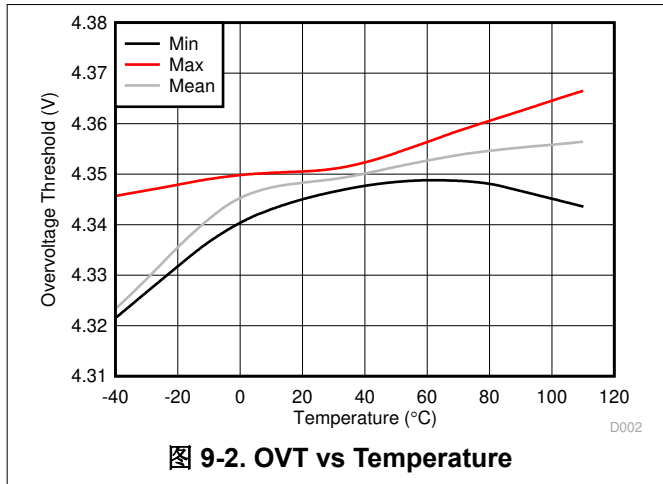
表 9-1. Parameters (continued)

PARAMETER	EXTERNAL COMPONENT	MIN	NOM	MAX	UNIT
Supply voltage filter capacitance	CVD		0.1		μF

9.2.2 Detailed Design Procedure

1. Determine the overvoltage protection and delay. Select a device with the corresponding thresholds.
2. Follow the application schematic (see 图 9-1) to connect the device.
3. Ensure both Vss pins are connected to the CELL - terminal on the PCB layout.

9.2.3 Application Curves



9.3 System Example

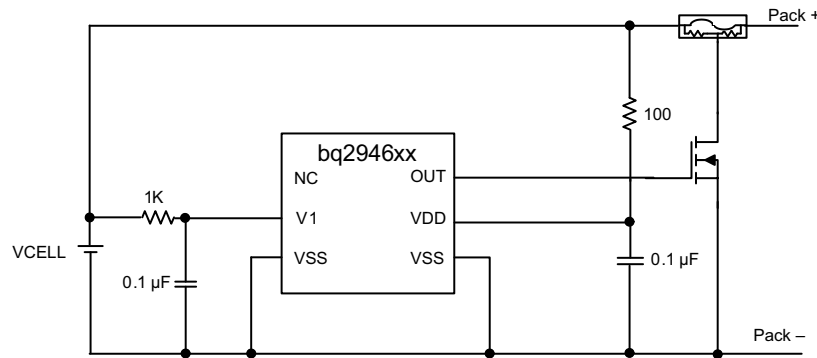


图 9-4. 1-Cell Configuration With Fixed Delay

Power Supply Recommendations

The maximum power of this device is 8 V on VDD.

9 Layout

9.1 Layout Guidelines

1. Ensure the RC filters for the V1 and VDD pins are placed as close as possible to the target terminal, reducing the tracing loop area.
2. The VSS pin should be routed to the CELL - terminal.
3. Ensure the trace connecting the fuse to the gate, source of the NFET to the Pack is sufficient to withstand the current during a fuse blown event.

9.2 Layout Example

Place the RC filters close to the device terminals

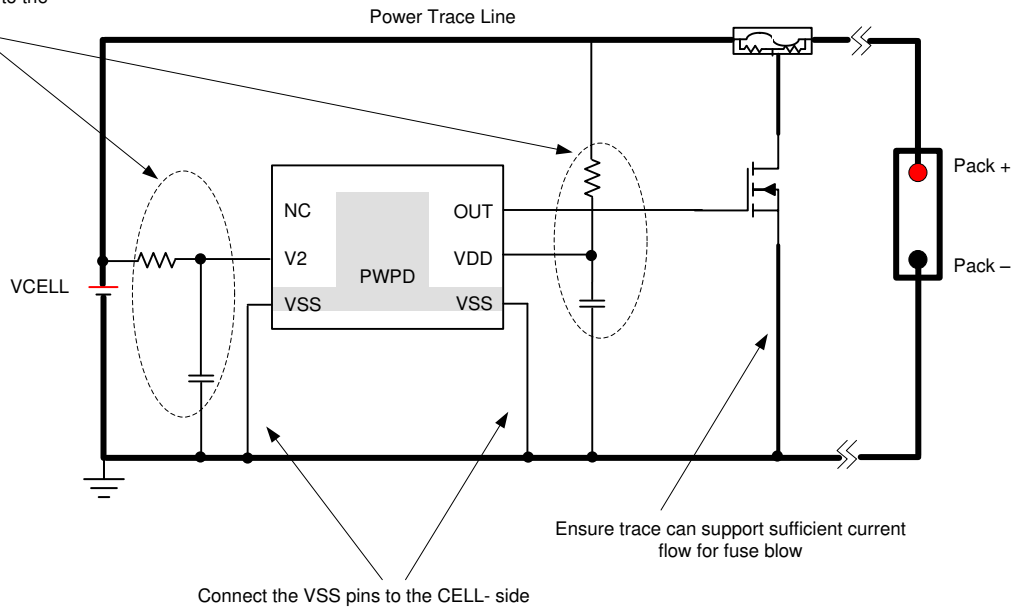


图 9-1. Layout Schematic

10 Device and Documentation Support

10.1 第三方产品免责声明

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10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

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TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

10.6 术语表

TI 术语表 本术语表列出并解释了术语、首字母缩略词和定义。

Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
BQ294602DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 110	4602	Samples
BQ294602DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 110	4602	Samples
BQ294604DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 110	4604	Samples
BQ294604DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 110	4604	Samples
BQ294624DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 110	4624	Samples
BQ294624DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 110	4624	Samples
BQ294682DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	Call TI NIPDAU	Level-1-260C-UNLIM	-40 to 110	4682	Samples
BQ294682DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 110	4682	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BQ294602DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294602DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294604DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294604DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294604DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294604DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294624DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294624DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294682DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294682DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

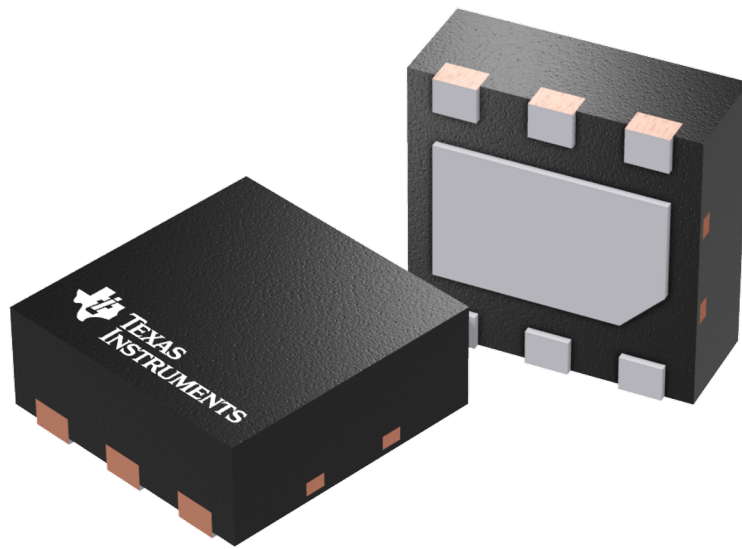
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ294602DRVR	WSON	DRV	6	3000	182.0	182.0	20.0
BQ294602DRVT	WSON	DRV	6	250	210.0	185.0	35.0
BQ294604DRVR	WSON	DRV	6	3000	210.0	185.0	35.0
BQ294604DRVR	WSON	DRV	6	3000	210.0	185.0	35.0
BQ294604DRVT	WSON	DRV	6	250	210.0	185.0	35.0
BQ294604DRVT	WSON	DRV	6	250	210.0	185.0	35.0
BQ294624DRVR	WSON	DRV	6	3000	182.0	182.0	20.0
BQ294624DRVT	WSON	DRV	6	250	182.0	182.0	20.0
BQ294682DRVR	WSON	DRV	6	3000	182.0	182.0	20.0
BQ294682DRVT	WSON	DRV	6	250	182.0	182.0	20.0

GENERIC PACKAGE VIEW

DRV 6

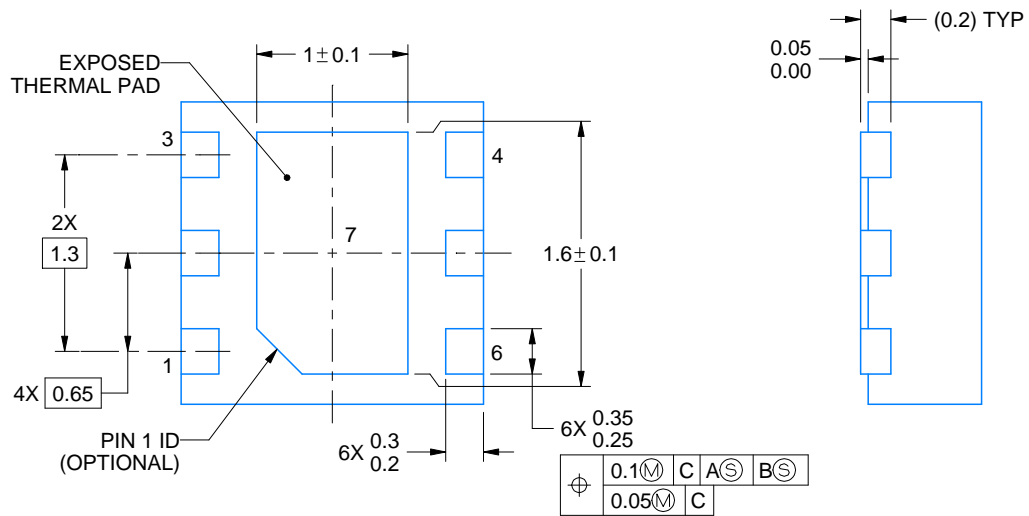
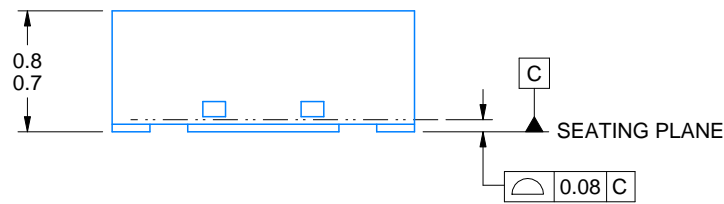
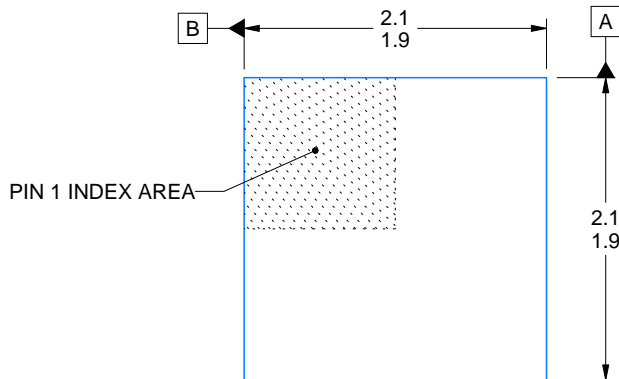
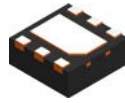
WSO - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

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NOTES:

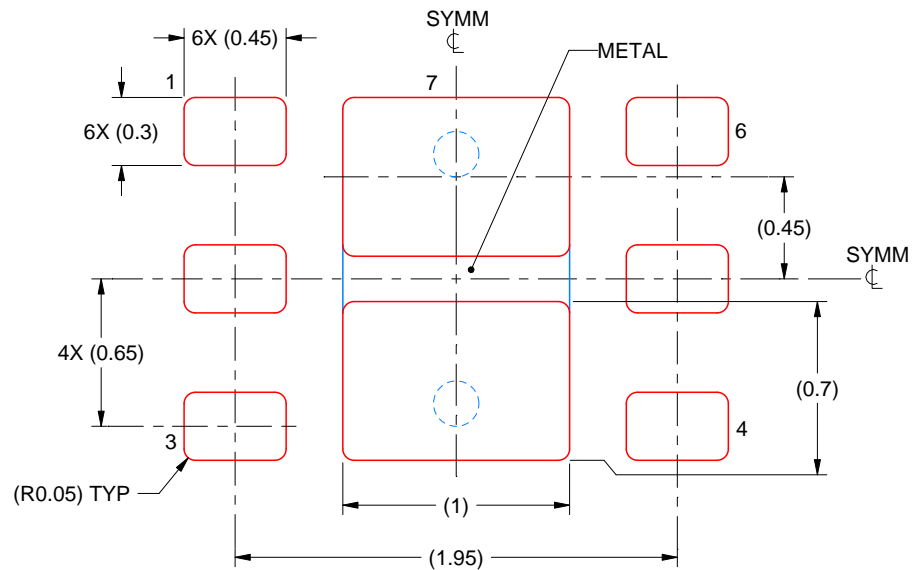
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE STENCIL DESIGN

DRV0006A

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD #7
88% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:30X

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NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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